

SPTECH Silicon NPN Power Transistor

BU406D

DESCRIPTION

- High Voltage: $V_{CEV} = 400V(\text{Min})$
- Low Saturation Voltage-
: $V_{CE(\text{sat})} = 1.0V(\text{Max.}) @ I_C = 5A$

APPLICATIONS

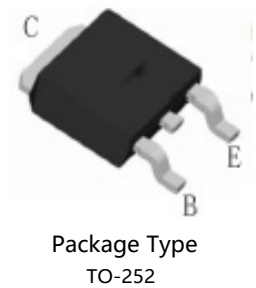
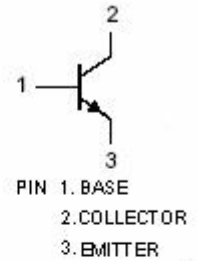
- Designed for use in horizontal deflection output stages of TV's and CRT's

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	400	V
V_{CEO}	Collector-Emitter Voltage	200	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	7	A
I_{CP}	Collector Current-Peak Repetitive	10	A
I_{CP}	Collector Current- Peak (10ms)	15	A
I_B	Base Current	4	A
P_C	Collector Power Dissipation @ $T_C = 25^\circ\text{C}$	65	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	2.08	$^\circ\text{C/W}$
$R_{th\ j-a}$	Thermal Resistance, Junction to Ambient	70	$^\circ\text{C/W}$



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ELECTRICAL CHARACTERISTICS

$T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEQ(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C= 50\text{mA}$; $I_B= 0$	150			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C= 5\text{A}$; $I_B= 0.8\text{A}$			1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C= 5\text{A}$; $I_B= 0.5\text{A}$			1.2	V
I_{CES}	Collector Cutoff Current	$V_{CE}= 400\text{V}$; $V_{BE}= 0$ $V_{CE}=250\text{V}$; $V_{BE}= 0$			5.0 0.1	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}= 6\text{V}$; $I_C= 0$			1.0	mA
h_{FE}	DC Current Gain	$I_C= 2\text{A}$; $V_{CE}= 5\text{V}$	60	70	80	
f_T	Current-Gain—Bandwidth Product	$I_C= 0.5\text{A}$; $V_{CE}= 10\text{V}$	10	30		MHz
t_f	Fall Time	$I_C= 5\text{A}$; $I_{B1}= -I_{B2}= 0.8\text{A}$			0.4	μs